



STB95NF03

N-CHANNEL 30V - 0.0065 Ω - 95A D²PAK
STripFET™ II POWER MOSFET

TYPE	V _{DSS}	R _{DS(on)}	I _D
STB95NF03	30 V	<0.007 Ω	80 A

- TYPICAL R_{DS(on)} = 0.0065 Ω
- STANDARD THRESHOLD DRIVE
- 100% AVALANCHE TESTED
- SURFACE-MOUNTING D²PAK (TO-263)
POWER PACKAGE IN TUBE (NO SUFFIX) OR
IN TAPE & REEL (SUFFIX "T4")

DESCRIPTION

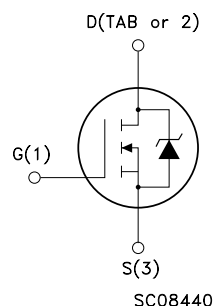
This Power MOSFET is the latest development of STMicroelectronics unique "Single Feature Size™" strip-based process. The resulting transistor shows extremely high packing density for low on-resistance, rugged avalanche characteristics and less critical alignment steps therefore a remarkable manufacturing reproducibility.

APPLICATIONS

- HIGH CURRENT, HIGH SPEED SWITCHING
- DC-DC & DC-AC CONVERTERS
- SOLENOID AND RELAY DRIVERS



INTERNAL SCHEMATIC DIAGRAM



ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{DS}	Drain-source Voltage (V _{GS} = 0)	30	V
V _{DGR}	Drain-gate Voltage (R _{GS} = 20 k Ω)	30	V
V _{GS}	Gate- source Voltage	± 20	V
I _D (*)	Drain Current (continuous) at T _C = 25°C	80	A
I _D	Drain Current (continuous) at T _C = 100°C	80	A
I _{DM} (•)	Drain Current (pulsed)	320	A
P _{tot}	Total Dissipation at T _C = 25°C	150	W
	Derating Factor	1	W/°C
dv/dt (1)	Peak Diode Recovery voltage slope	3.0	V/ns
E _{AS} (2)	Single Pulse Avalanche Energy	720	mJ
T _{stg}	Storage Temperature	-55 to 175	°C
T _j	Operating Junction Temperature		

(•) Pulse width limited by safe operating area.

(*) Current Limited by Package

(1) I_{SD} ≤ 95A, di/dt ≤ 150A/μs, V_{PD} ≤ V(BR)_{DSS}, T_j ≤ T_{JMAX}.

(2) Starting T_j = 25 °C, I_D = 47.5A, V_{PD} = 25V

THERMAL DATA

Rthj-case	Thermal Resistance Junction-case	Max	1	°C/W
Rthj-amb	Thermal Resistance Junction-ambient	Max	62.5	°C/W
T _l	Maximum Lead Temperature For Soldering Purpose		300	°C

ELECTRICAL CHARACTERISTICS (T_{case} = 25 °C unless otherwise specified)**OFF**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{(BR)DSS}	Drain-source Breakdown Voltage	I _D = 250 µA V _{GS} = 0	30			V
I _{DSS}	Zero Gate Voltage Drain Current (V _{GS} = 0)	V _{DS} = Max Rating V _{DS} = Max Rating T _C = 125°C			1 10	µA µA
I _{GSS}	Gate-body Leakage Current (V _{DS} = 0)	V _{GS} = ± 20 V			±100	nA

ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} I _D = 250 µA	2		4	V
R _{DS(on)}	Static Drain-source On Resistance	V _{GS} = 10 V I _D = 45 A		0.0065	0.0070	Ω

DYNAMIC

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
g _{fs} (*)	Forward Transconductance	V _{DS} = 15 V I _D = 45 A		50		S
C _{iss}	Input Capacitance	V _{DS} = 25V f = 1 MHz V _{GS} = 0		2450		pF
C _{oss}	Output Capacitance			880		pF
C _{rss}	Reverse Transfer Capacitance			170		pF

ELECTRICAL CHARACTERISTICS (continued)

SWITCHING ON (*)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r	Turn-on Time Rise Time	$V_{DD} = 15\text{ V}$ $I_D = 47.5\text{ A}$ $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$		20 195		ns ns
Q_g Q_{gs} Q_{gd}	Total Gate Charge Gate-Source Charge Gate-Drain Charge	$V_{DD}=15\text{ V}$ $I_D=95\text{ A}$ $V_{GS}=10\text{ V}$		59 18 21	70	nC nC nC

SWITCHING OFF(*)

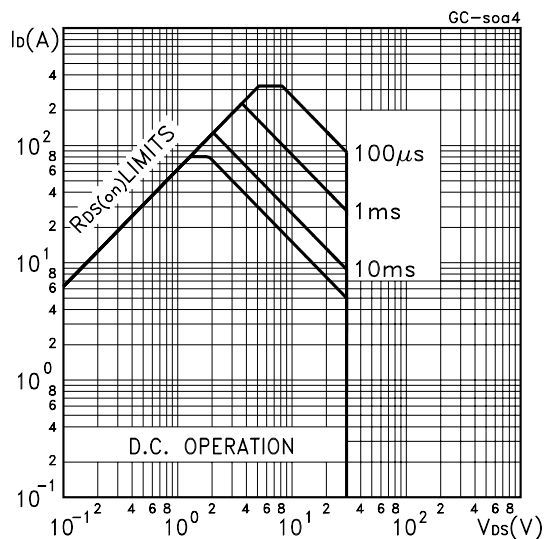
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(off)}$ t_f	Turn-off Delay Time Fall Time	$V_{DD} = 20\text{ V}$ $I_D = 47.5\text{ A}$ $R_G = 4.7\ \Omega$, $V_{GS} = 10\text{ V}$		35 35		ns ns

SOURCE DRAIN DIODE(*)

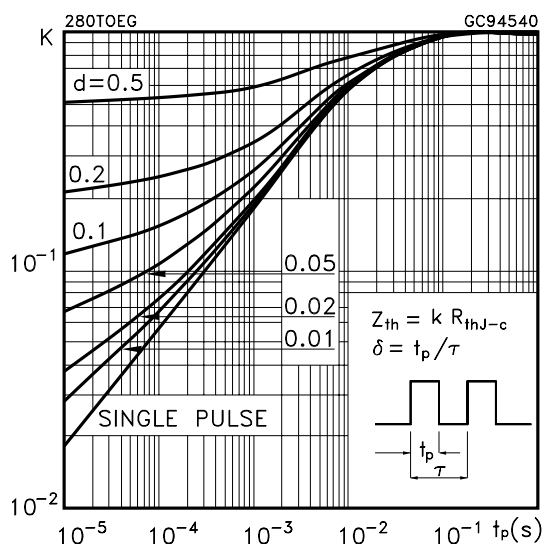
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_{SD} $I_{SDM} (*)$	Source-drain Current Source-drain Current (pulsed)				95 320	A A
$V_{SD} (*)$	Forward On Voltage	$I_{SD} = 95\text{ A}$ $V_{GS} = 0$			1.3	V
t_{rr} Q_{rr} I_{RRM}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_{SD} = 95\text{ A}$ $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 20\text{ V}$ $T_J = 150^\circ\text{C}$ (see test circuit, Figure 5)		60 120 4		ns nC A

(*) Pulsed: Pulse duration = 300 μs , duty cycle 1.5 %.(•) Pulse width limited by T_{Jmax}

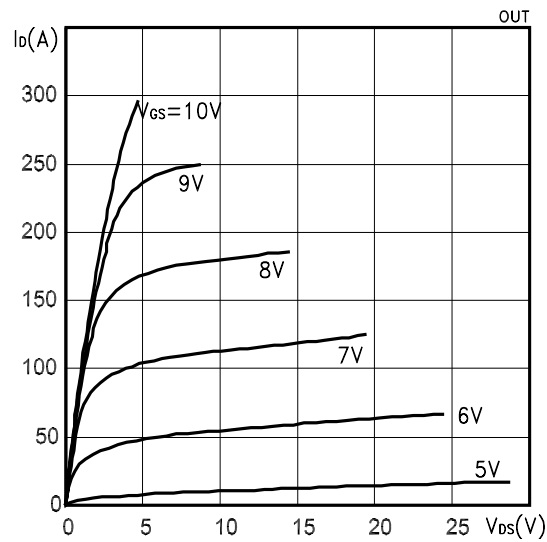
Safe Operating Area



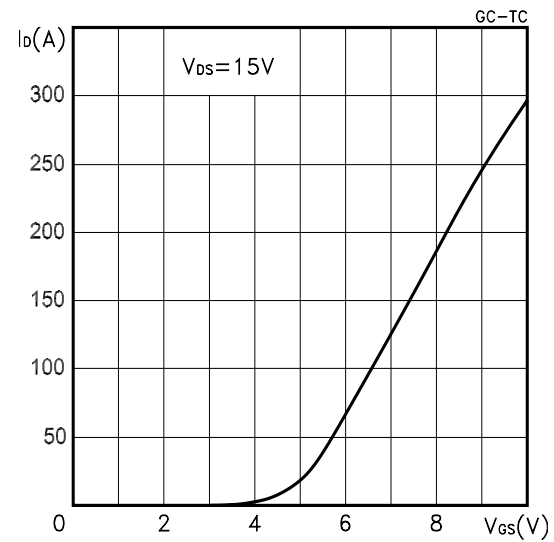
Thermal Impedance



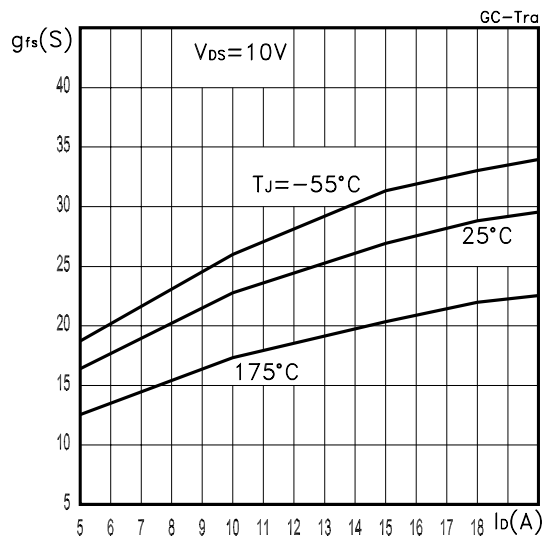
Output Characteristics



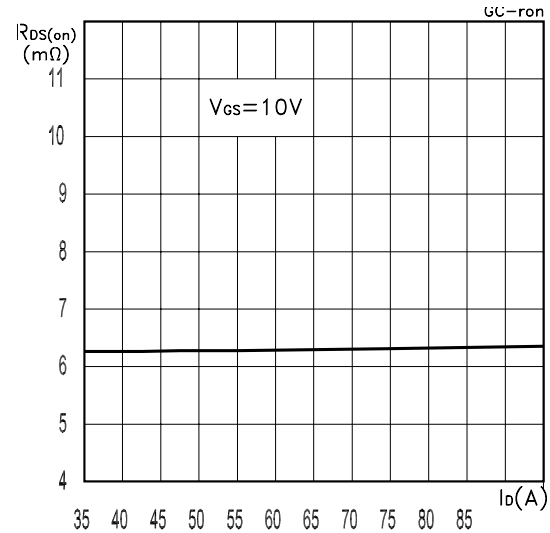
Transfer Characteristics



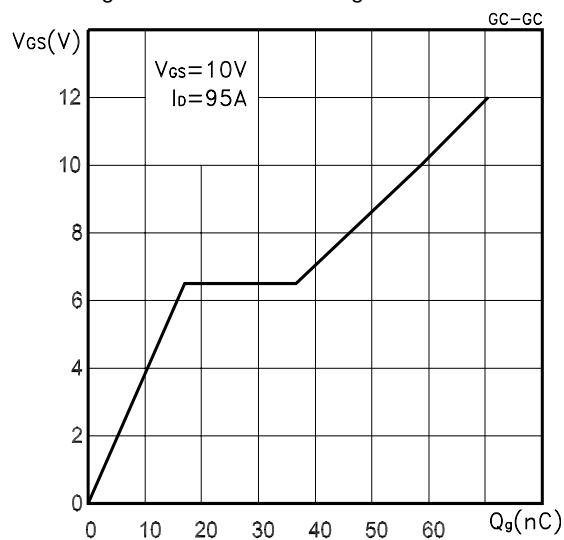
Transconductance



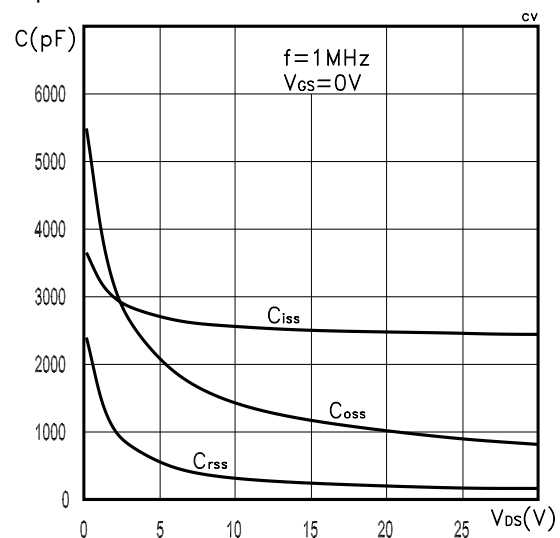
Static Drain-source On Resistance



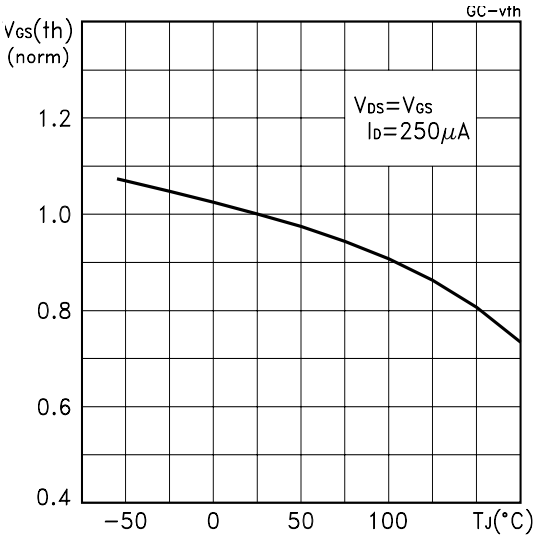
Gate Charge vs Gate-source Voltage



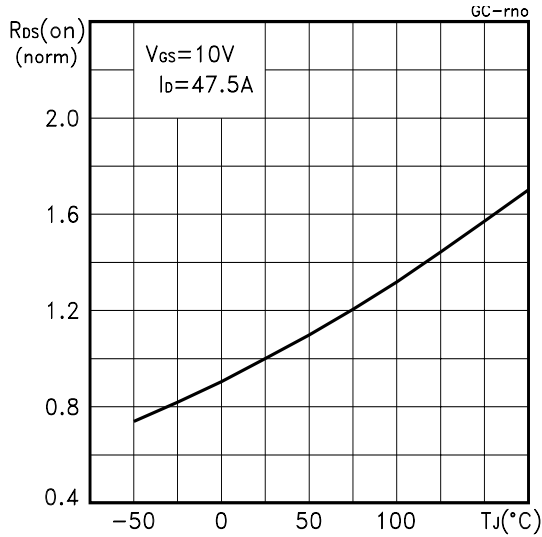
Capacitance Variations



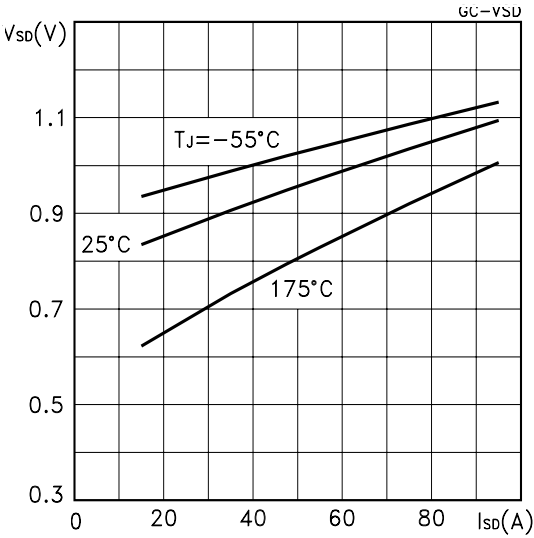
Normalized Gate Threshold Voltage vs Temperature



Normalized on Resistance vs Temperature



Source-drain Diode Forward Characteristics



Normalized Breakdown Voltage vs Temperature.

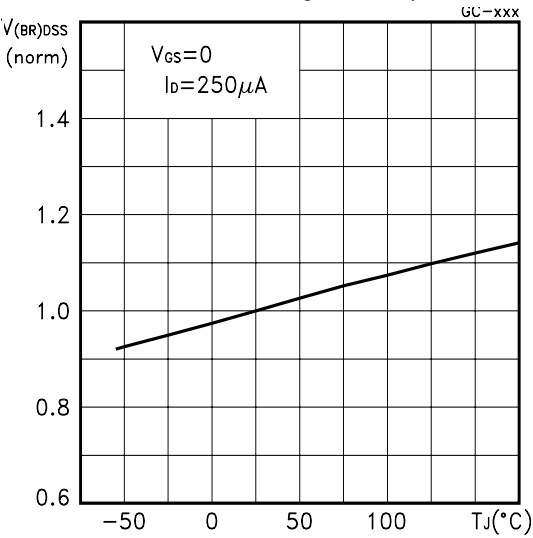


Fig. 1: Unclamped Inductive Load Test Circuit

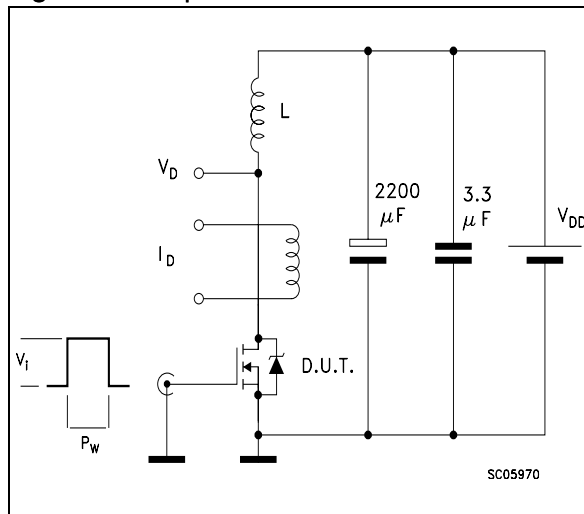


Fig. 2: Unclamped Inductive Waveform

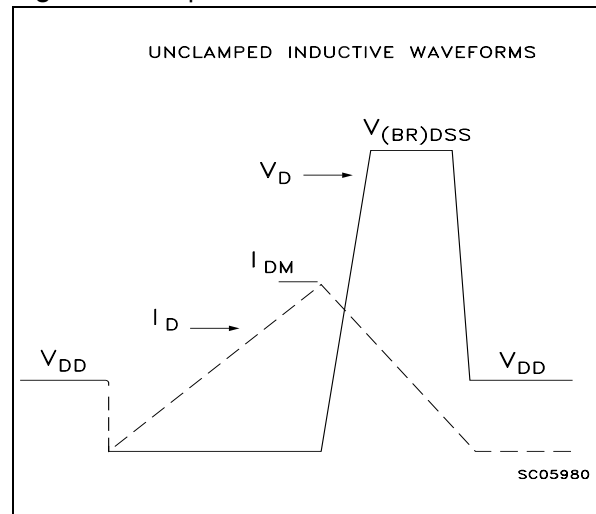


Fig. 3: Switching Times Test Circuits For Resistive Load

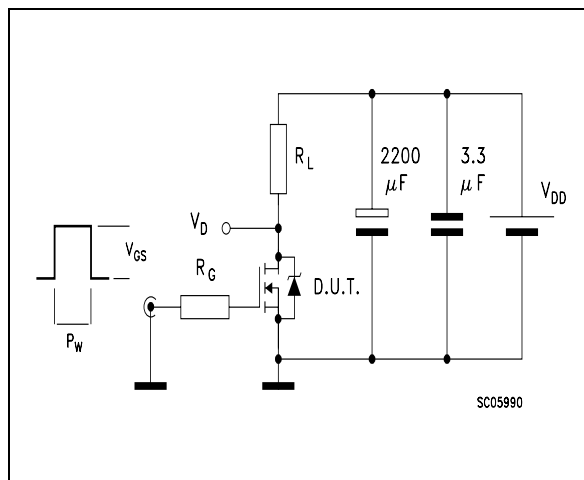


Fig. 4: Gate Charge test Circuit

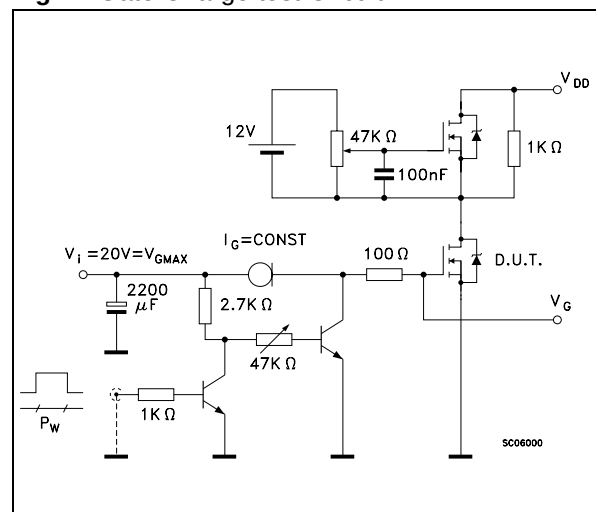
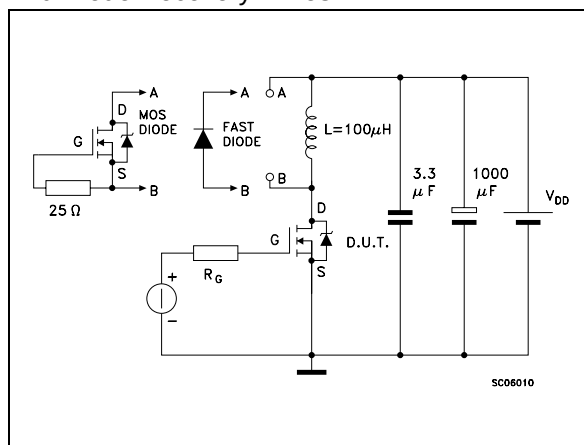
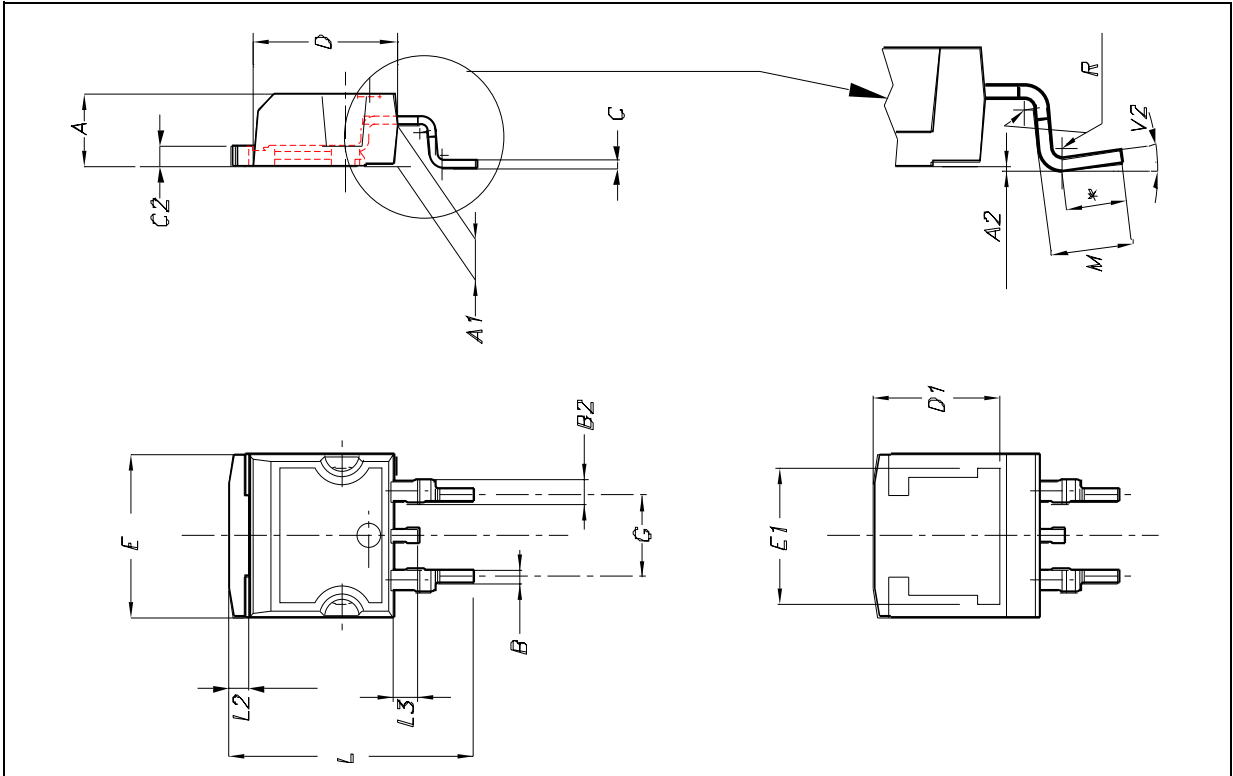


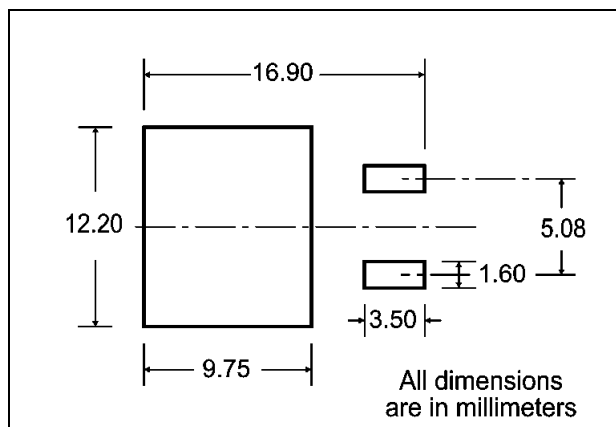
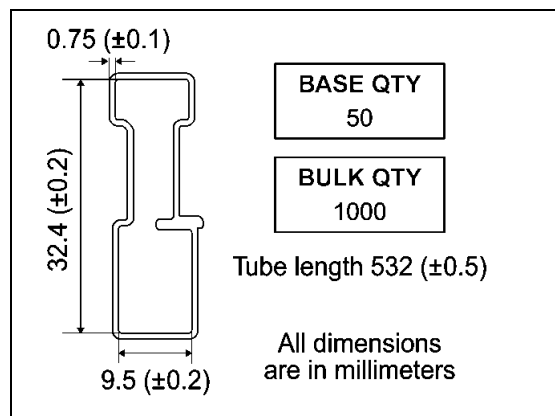
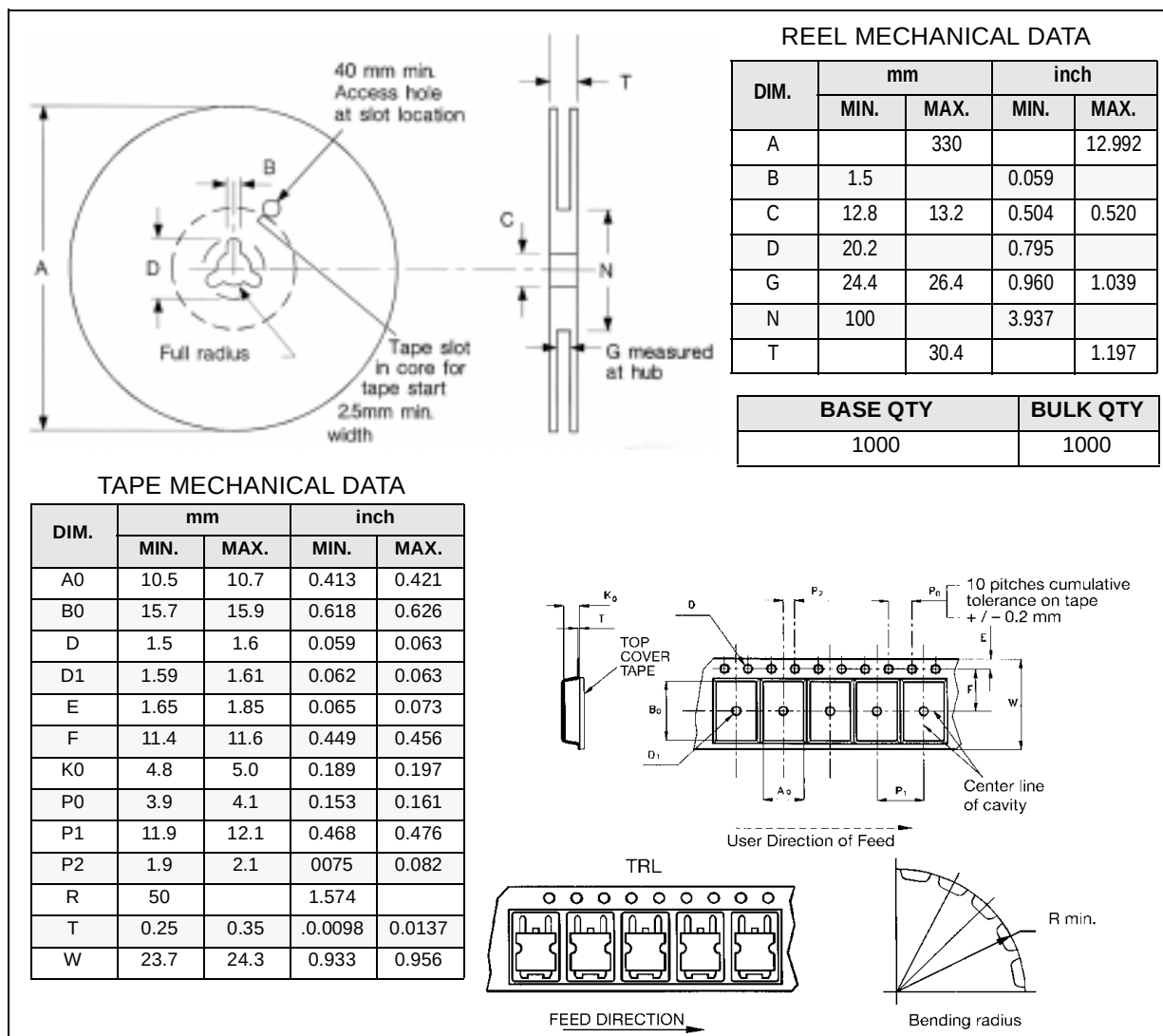
Fig. 5: Test Circuit For Inductive Load Switching And Diode Recovery Times



D²PAK MECHANICAL DATA

DIM.	mm.			inch.		
	MIN.	TYP.	MAX.	MIN.	TYP.	TYP.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.028		0.037
B2	1.14		1.7	0.045		0.067
C	0.45		0.6	0.018		0.024
C2	1.21		1.36	0.048		0.054
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.394		0.409
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.591		0.624
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.069
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		8°	0°		8°



D²PAK FOOTPRINT**TUBE SHIPMENT (no suffix)*****TAPE AND REEL SHIPMENT (suffix "T4")***

* on sales type

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is registered trademark of STMicroelectronics
All other names are the property of their respective owners.

® 2003 STMicroelectronics - All Rights Reserved

STMicroelectronics GROUP OF COMPANIES

Australia - Belgium - Brazil - Canada - China - Czech Republic - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan -
Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

www.st.com